



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 250270US2SDIV	SERIAL NO. 10/798,571		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Minoru AMANO, et al.					
		FILING DATE March 12, 2004	GROUP				
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<i>MH</i>	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, pages 128-129, "TA 7.2 A 10NS READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000					
<i>MH</i>	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997					
<i>MH</i>	AY	M. SATO, et al., Jpn. J. Appl. Phys., vol. 36, part 2, no. 2B, pages L200-L201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997					
<i>MH</i>	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys., vol. 36, part 2, no. 10B, pages L1380-L1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997			<input type="checkbox"/> Additional References sheet(s) attached		
Examiner <i>Minoru Amano</i>				Date Considered <i>11/15/04</i>			

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.